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http://www.springer.com/978-3-319-09673-5

Micro and Nanophotonics for Semiconductor Infrared Detectors
Towards an Ultimate Uncooled Device
Jakšić, Z.
2014, XXI, 258 p. 152 illus., 41 illus. in color., Hardcover
ISBN: 978-3-319-09673-5